

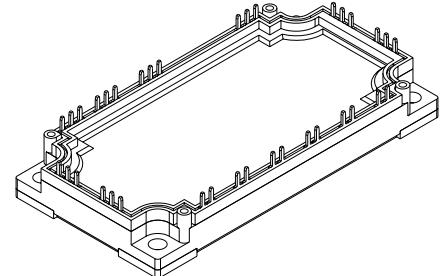
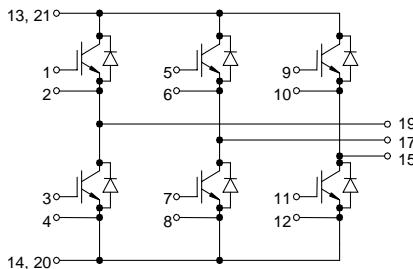
IGBT Modules

Sixpack

Short Circuit SOA Capability

Square RBSOA

I_{C25} = 170 A
 V_{CES} = 600 V
 $V_{CE(sat)\text{ typ.}}$ = 2.0 V



IGBTs

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	600		V
V_{GES}		± 20		V
I_{C25}	$T_C = 25^\circ\text{C}$	170		A
I_{C80}	$T_C = 80^\circ\text{C}$	115		A
RBSOA	$V_{GE} = \pm 15 \text{ V}$; $R_G = 1.5 \Omega$; $T_{VJ} = 125^\circ\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 300$		A
		$V_{CEK} \leq V_{CES}$		
t_{sc} (SCSOA)	$V_{CE} = V_{CES}$; $V_{GE} = \pm 15 \text{ V}$; $R_G = 1.5 \Omega$; $T_{VJ} = 125^\circ\text{C}$ non-repetitive	10		μs
P_{tot}	$T_C = 25^\circ\text{C}$	515		W

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 150 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.0	2.5	V
		2.3		V
$V_{GE(th)}$	$I_C = 3 \text{ mA}$; $V_{GE} = V_{CE}$	4.5		V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.5	mA
			1.1	mA
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$		400	nA
$t_{d(on)}$ t_i $t_{d(off)}$ t_f E_{on} E_{off}	$\left. \begin{array}{l} \text{Inductive load, } T_{VJ} = 125^\circ\text{C} \\ V_{CE} = 300 \text{ V}; I_C = 150 \text{ A} \\ V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega \end{array} \right\}$	125		ns
		30		ns
		225		ns
		35		ns
		2.3		mJ
		4.6		mJ
C_{ies} Q_{Gon}	$V_{CE} = 25 \text{ V}$; $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$ $V_{CE} = 300 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 150 \text{ A}$	6.5		nF
		tbd		nC
R_{thJC}	(per IGBT)		0.24	K/W

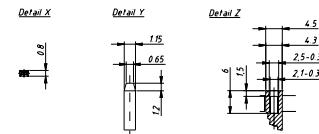
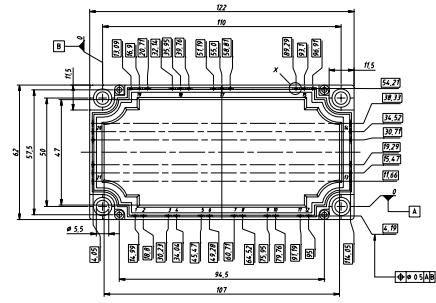
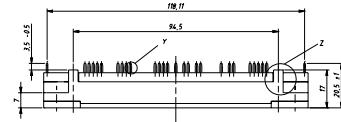
IXYS reserves the right to change limits, test conditions and dimensions.

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Diodes

Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	210	A	
I _{F80}	T _C = 80°C	130	A	

Dimensions in mm (1 mm = 0.0394")



Higher magnification see outlines.pdf

Module

Symbol	Conditions	Maximum Ratings		
T _{VJ}		-40...+150	°C	
T _{stg}		-40...+125	°C	
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500	V~	
M _d	Mounting torque (M5)	3 - 6	Nm	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R _{pin-chip}		1.8		mΩ
d _s	Creepage distance on surface	10		mm
d _A	Strike distance in air	10		mm
R _{thCH}	with heatsink compound	0.01		K/W
Weight		300		g